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Customer No.: 26263

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Etsuo Morita

Group Art Unit: 1765

Application No.: 09/728,193

Examiner: Matthew J. Song

Confirmation No.: 4426

Filed: November 30, 2000

For: METHOD OF MANUFACTURING CRYSTAL OF III-V COMPOUND OF THE NITRIDE SYSTEM, CRYSTAL SUBSTRATE OF III-V COMPOUND OF THE NITRIDE SYSTEM, CRYSTAL FILM OF III-V COMPOUND OF THE NITRIDE SYSTEM, AND METHOD OF MANUFACTURING DEVICE

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner Of Patents and Trademarks
Washington, D.C. 20231

Sir:

In response to the Non-Final Office Action dated August 30, 2002, Paper No. 4, one month extended until December 30, 2002 along with a Petition for Extension of Time and the appropriate fee, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 1, prior to the heading "BACKGROUND OF THE INVENTION", please insert the following paragraph:

A1
The present application claims priority from Japanese Patent Application No. 11-341637, dated December 1, 1999.

[Page 6, please replace the first full paragraph with the following new paragraph:]

A2
In the method of manufacturing a crystal of a III-V compound of the nitride system, the crystal substrate of a III-V compound of the nitride system, the crystal film of a III-V compound of the nitride system and the method of manufacturing a device according to the invention, it is ensured that the development of dislocations is prevented in a region where a plurality of patterns does not overlie one